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Phys. Rev. Lett. **106**, 126803 — Published 22 March 2011

DOI: [10.1103/PhysRevLett.106.126803](https://doi.org/10.1103/PhysRevLett.106.126803)

Quantum Hall Effect from the Topological Surface States of Strained Bulk HgTe

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We report transport studies on a three dimensional, 70 nm thick HgTe layer, which is strained by epitaxial growth on a CdTe substrate. The strain induces a band gap in the otherwise semi-metallic HgTe, which thus becomes a three dimensional topological insulator. Contributions from residual bulk carriers to the transport properties of the gapped HgTe layer are negligible at mK temperatures. As a result, the sample exhibits a quantized Hall effect that results from the 2D single cone Dirac-like topological surface states.

PACS numbers: 73.25.+i, 73.43.-f, 73.20.At

The discovery of two (2D) and three dimensional (3D) topological insulators (TI)[1–10] has generated strong activity in the condensed matter physics community[11, 12]. Current research on 3D TIs is mostly focused on Bi₂Te₃, Bi₂Se₃ and Sb₂Te₃ compounds[8–10] due to their simple Dirac-like surface states, which have been observed by angle resolved photoemission spectroscopy (ARPES) and scanning tunneling microscopy[11]. However, these compounds show strong defect doping and low carrier mobility, and the observation of surface charge transport is obscured by the bulk conductivity. Many of the predicted novel properties of a 3D TI, such as the quantized magneto-electric effect[13, 14] and the surface Majorana fermions[15], can only be observed when bulk carriers are negligible compared to the surface states. Experimentally reaching the intrinsic TI regime, where bulk carriers are absent, is now the central focus of the field.

The two dimensional TI state was first predicted and observed in 2D HgTe quantum wells (QW)[1, 3], and non-local transport measurements demonstrate edge state transport without any contributions from 2D bulk carriers.[16] 3D HgTe is a semi-metal which is charge-neutral when the Fermi energy is at the touching point between the light-hole and heavy-hole Γ_8 bands at the Brillouin zone center. A unique property of the band structure of HgTe is the energetic inversion of the Γ_6 and Γ_8 band ordering, which is the origin of the quantum spin Hall effect in 2D HgTe/CdTe QWs[3]. Due to the band inversion, 3D HgTe is also expected to have Dirac-like surface states[17, 18], but since the material is semi-metallic, this state is always coupled to metallic bulk states. With applied strain, a gap opens up between the light-hole and heavy-hole bands, so that strained 3D HgTe is expected to be a 3D TI[4, 19]. In this paper we demonstrate experimentally that a gap opens up in in-plane strained 3D HgTe bulk layers grown by molecular beam epitaxy (MBE), and we reach the much sought after intrinsic TI regime in a material with negligible bulk carriers. In this regime, the Hall effect of the 3D HgTe bulk layer is quantized, due to the

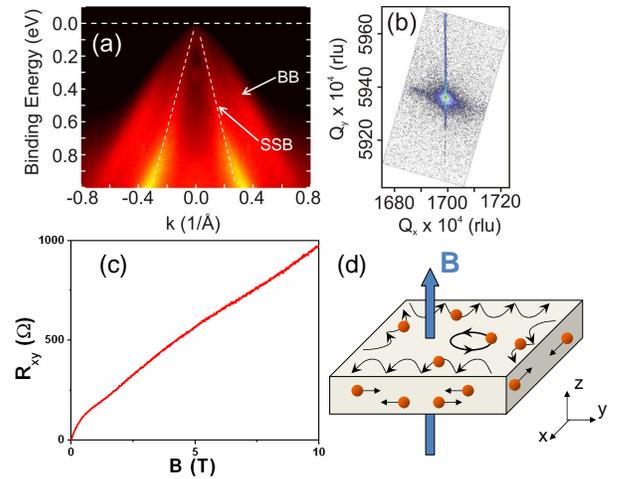


FIG. 1: Supporting characterization experiments. (a) ARPES measurements on a relaxed, 1 μm thick HgTe sample. The dispersion of the surface state (SSB) and bulk bands (BB) are indicated by the arrows; (b) Reciprocal space map in the region of the [115] reflex of the 70 nm thick HgTe sample demonstrating that the epilayer is coherently strained; (c) Hall resistance as a function of magnetic field of the semi-metallic 1 μm thick sample; (d) Schematic picture of the coexistence of the chiral edge states from the upper and lower surfaces and the non-chiral metallic modes at the side surfaces. The magnetic field is perpendicular to the upper and lower surfaces, but parallel to the four side surfaces.

contributions from the surface states only. Theoretical considerations are in agreement with the experimental results and confirm the transport through 2D surface states with Dirac type dispersion.

HgTe bulk samples have been grown by MBE on CdTe substrates, which have a lattice constant that is 0.3 % larger than that of bulk HgTe (0.646 nm). At this mismatch, the critical thickness for lattice relaxation is around 200 nm, implying that for thinner HgTe the epi-

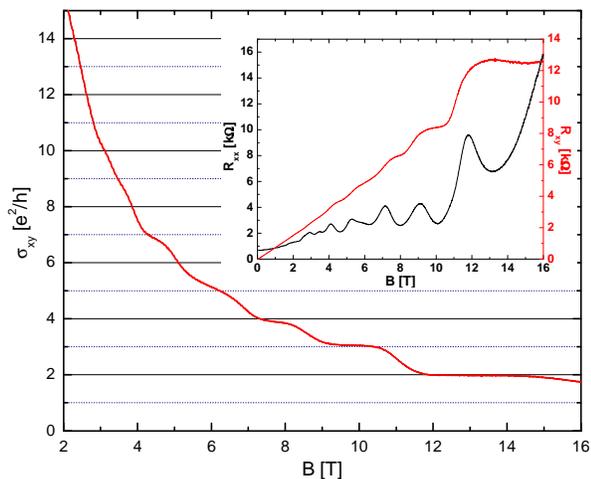


FIG. 2: Transport data on the strain-gapped 70 nm thick HgTe sample. The Hall conductivity of the 70 nm thick HgTe sample measured at 50 mK shows plateaus at the quantized values. The inset shows the Hall resistance R_{xy} , together with the longitudinal resistance R_{xx} .

layer adopts the lateral lattice constant of the substrate, while in thicker layers the strain is relaxed by the formation of dislocations.

To provide evidence for the occurrence of the topological surface state, we first show an ARPES measurement on a 1 μm thick HgTe layer in [Fig. 1 (a)]. In this layer, the lattice strain is fully relaxed, and the surface has the lattice constant of unstrained bulk material. The figure clearly shows the presence of the predominantly linearly dispersing surface state band (SSB), coexisting with bulk bands (BBs) (more data on these assignments can be found in the supplementary material). According to the theoretical analysis in Ref. (19), the surface states originate from the inversion between the Γ_8 light-hole and Γ_6 electron bands, while the bulk bands, which appear nearly at the same energy range with the surface states, correspond to the Γ_8 heavy-hole band.

Since the relaxed sample is a semi-metal and thus not a TI in the strict sense, we have grown a thinner sample, which is only 70 nm thick, thin enough for the epitaxial strain due to the lattice mismatch with the substrate to coherently strain the sample, thus opening up a bulk insulating gap. Fig. 1 (b) shows a high resolution X-ray diffraction map of the [115] reflex of this sample in units of reciprocal lattice space vectors. The bright spot in the center of this graph is the reflex from the substrate, while the thin vertical line stems from the HgTe epilayer. The absence of any relaxation of the reciprocal lattice vector \mathbf{Q}_x for the epilayer is direct evidence that this sample is fully strained.[20] The deformation potentials of (Hg,Cd)Te have been reported in the literature[21]; using these values and the 0.3 % lattice mismatch we calculate an energy gap of the order of ~ 22 meV for

fully strained HgTe on CdTe, using an eight band $\mathbf{k}\cdot\mathbf{p}$ model [22]. We believe this energy gap to be the optimal gap value that can be obtained in HgTe. In principle substrates with a larger lattice mismatch would induce a larger gap, however, these are not readily available. In addition larger strain would also reduce the maximum thickness the HgTe layer can sustain without strain relaxation.

For transport experiments, we have subsequently patterned parts of both wafers into Hall-geometry devices with a mesa of 200 μm width and 600 μm length, using argon ion etching. The magneto transport of the samples has been investigated at a base temperature of 50 mK, in magnetic fields up to 16 T. In the 1 μm thick sample, the Hall data indicates that bulk conductance dominates the transport. Fig. 1 (c) shows that for this sample we observe a non-monotonic dependence of the Hall voltage, which is characteristic for the multi-carrier transport expected from a semi-metal. Much more interesting behavior is observed for the 70 nm-thick sample, of which the longitudinal and Hall resistance are shown in the inset of Fig. 2. From the low field data, the electron mobility can be extracted, and estimated as 34000 $\text{cm}^2/(\text{V}\cdot\text{s})$, which is significantly higher than that observed in Bi_2Se_3 and Bi_2Te_3 [23, 24]. At high magnetic fields, the longitudinal and Hall resistance exhibit distinct features which are characteristic for a 2D electron system (2DES): the Hall resistance R_{xy} shows plateaus at the same magnetic fields where the longitudinal resistance R_{xx} develops a minimum (inset of Fig. 2). Additionally, the Hall resistance R_{xy} shows the expected 2D quantized plateau values, which become clearer in a conductivity plot (Fig. 2).

Compared with the quantum Hall effect of an ordinary 2DES, two unusual observations should be emphasized, which indicate that the observed quantum Hall plateaus indeed result from the Dirac-type dispersion of the topological surface states. First, at low magnetic fields, a sequence of Hall plateaus develops with odd filling factors, $\nu = 9, 7, \text{ and } 5$, before at higher field the sequence is continued with $\nu = 4, 3, \text{ and } 2$. The occurrence of odd-number filling factors at low magnetic field indicates the presence of a zero mode (a Landau level at zero energy) due to the linear dispersion of Dirac fermions, as has also been found in graphene[25] and in HgTe/CdTe QWs with a critical thickness of 6.3 nm[26]. A 70nm thick layer can safely be regarded as a 3D material; the confinement energies of bulk carriers are sufficiently small that Hall quantization effects would be washed out by multi-subband averaging. We thus assume that the Hall plateaus result from the topological surface states, and use a model with two Dirac cones, one on the top (vacuum) and one on the bottom (CdTe interface) to describe the system (see additional online material for details). Because massless Dirac fermions in a magnetic field always exhibit a zero mode, the Hall conductance of a single Dirac cone is given by $\sigma_{xy} = (n + \frac{1}{2})e^2/h$,

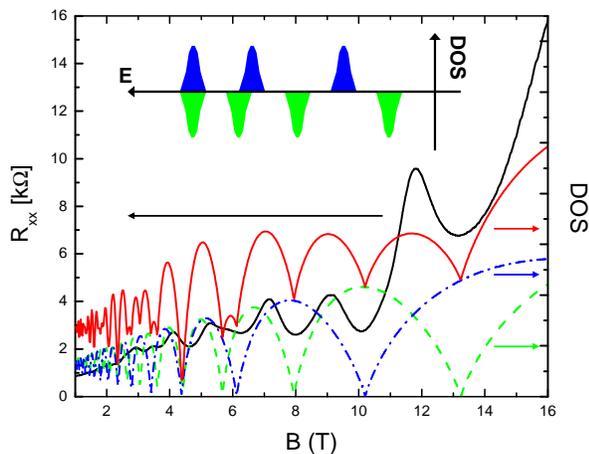


FIG. 3: Comparison between the calculated density of states (DOS) and the measured Shubnikov-de Haas oscillations. The DOS are calculated for a two Dirac cones model for the surface states with one Dirac cone (at the CdTe interface) having a carrier density $3.7 \times 10^{11} \text{cm}^{-2}$ (blue dashed-dotted line) and the other (the surface facing vacuum) $4.8 \times 10^{11} \text{cm}^{-2}$ (green dashed line). The sum of the DOS for the two Dirac cones (red line) compares well with the measured longitudinal resistance R_{xx} (black line). The inset shows the Landau ladders of the Dirac fermions on both surfaces.

where $n = n_t$ or $n = n_b$ (for the top and bottom surfaces, respectively) is always an integer[4, 13]. The fractional factor of $\frac{1}{2}$ in the Hall conductance σ_{xy} is a consequence of the quantized bulk topological term in the electromagnetic action[13], and is independent of the microscopic details. When top and the bottom surface have the same filling factor, *i.e.* $n = n_t = n_b$, the total Hall conductance is given by $\sigma_{xy}^T = (2n + 1)e^2/h$. Therefore, within the two Dirac cone model, the odd filling factor at low magnetic fields can be naturally explained assuming both surfaces have the same density. The appearance of an even filling factor at high magnetic field indicates that the degeneracy is removed. In an ordinary 2D electron gas, such a lift of degeneracy usually occurs due to Zeeman coupling. However, Zeeman coupling cannot lift the degeneracy in inversion symmetric Dirac cones on the top and bottom surface of a topological insulator. As we explain in the supplementary material, this is because the inversion symmetry is preserved by the magnetic field. The Landau levels from the top and bottom surface states will remain degenerate as long as the hybridization between the two surface states is negligible. For a thickness of 70nm, hybridization between the top and bottom surfaces can be neglected since the surface state width is around 2~3nm. Thus we conclude that the inversion symmetry breaking is necessary for the explanation of the Landau level splitting. In practice, the different electrostatic environments of both surfaces break the inversion symmetry and lead to different densities at both surfaces. This then leads to different Landau

filling factors for the top and bottom surfaces at high magnetic fields, and the visibility of even filling factors at high fields results from the increased energy splitting between adjacent Landau levels at lower filling factors in a Dirac system, as schematically indicated in the inset of Fig. 3. A calculation of the density of states in a magnetic field from a two Dirac cones model with an inversion breaking term indeed agrees well with the minima of the Shubnikov-de Haas oscillation, as shown in Fig. 3 (see additional online material for details). From the fit, we obtain very reasonable carrier densities of $3.7 \times 10^{11} \text{cm}^{-2}$ for the bottom (CdTe interface) and $4.8 \times 10^{11} \text{cm}^{-2}$ for the top surfaces, respectively. We note that the carrier densities found here also imply we can neglect any effects from bulk carriers - if the amount carriers found here would be evenly distributed over the 70 nm slab this would result in an overall 2D density of $\sim 10^{10} \text{cm}^{-2}$, yielding a very different quantum Hall behavior.

The second observation is that the minima in R_{xx} do not approach zero even at the highest magnetic fields although the Hall resistance is quantized and the plateaus have the expected resistance value. This indicates that besides the chiral edge modes from the quantum Hall effect, there are other modes contributing to the longitudinal, but not the Hall transport. A plausible candidate are the metallic states at the side surfaces[27]. While the above two Dirac cone model only takes the top and bottom surfaces explicitly into account, the topological surface states also occur on the four side surfaces, which see a parallel, rather than perpendicular, magnetic field. Consequently, at the side surfaces the Dirac points are not gapped, but only shifted by the applied magnetic field. Thus, the surface states at the side surfaces will remain metallic in magnetic field and coexist with the chiral edge states, as shown schematically in Fig 1(d). This provides a backscattering mechanism when the transport on the top and bottom surfaces is in the quantum Hall regime[27]. A more systematic study of the influence of the residual bulk conductivity and side surface states is required to fully understand the quantitative behavior of R_{xx} and R_{xy} , which is beyond the scope of the present letter.

In summary, we have experimentally reached the much sought after regime of the intrinsic 3D topological insulator with negligible bulk carriers, in epitaxially strained 3D HgTe sample. Our observation of a quantized Hall conductance in a 3D sample conclusively demonstrates a key feature of 3D topological insulators. A simple model with two Dirac cones is proposed to understand the most salient features of the transport measurement qualitatively. The quality of our sample should be sufficient to observe the quantized topological magnetoelectric effect[13], and directly determine the 3D topological invariant experimentally.

We acknowledge useful discussions with G. Astakhov, J.E. Moore and A.H. MacDonald. This work was sup-

ported by the German Research Foundation DFG (SPP 1285 Halbleiter Spintronik, DFG-JST joint research program, and grants AS327/2 (E.G.N.) and HA5893/1-1(E.M.H.)), the Alexander von Humboldt Foundation (C.X.L. and S.C.Z.), the EU ERC-AG program (L.W.M.) and the US Department of Energy, Office of Basic Energy Sciences, Division of Materials Sciences and Engineering, under contract DE-AC02-76SF00515 (S.C.Z).

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